

Silicon PNP Power Transistors

BDW84/84A/84B/84C/84D

DESCRIPTION

- With TO-3PN package
- Complement to type BDW83/83A/83B/83C/83D
- DARLINGTON
- High DC current gain

APPLICATIONS

- For use in power linear and switching applications.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

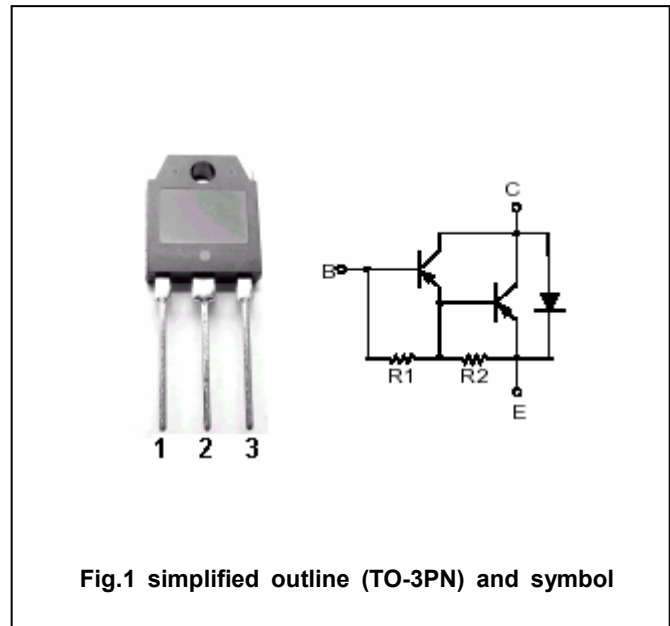


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BDW84	-45	V
		BDW84A	-60	
		BDW84B	-80	
		BDW84C	-100	
		BDW84D	-120	
V_{CEO}	Collector-emitter voltage	BDW84	-45	V
		BDW84A	-60	
		BDW84B	-80	
		BDW84C	-100	
		BDW84D	-120	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-15	A
I_B	Base current		-0.5	A
P_C	Collector power dissipation	$T_c=25^\circ\text{C}$	150	W
		$T_a=25^\circ\text{C}$	3.5	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

Silicon PNP Power Transistors

BDW84/84A/84B/84C/84D

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	BDW84	I _C =-30mA, I _B =0			-45
		BDW84A				-60
		BDW84B				-80
		BDW84C				-100
		BDW84D				-120
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-6A, I _B =-12mA			-2.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-15A, I _B =-150mA			-4.0	V
V _{BE}	Base-emitter on voltage	I _C =-6A; V _{CE} =-3V			-2.5	V
I _{CBO}	Collector cut-off current	BDW84	V _{CB} =-45V, I _E =0 T _C =150 °C			-0.5
		BDW84A				-5.0
		BDW84B				-0.5
		BDW84C				-5.0
		BDW84D				-0.5
I _{CEO}	Collector cut-off current	BDW84	V _{CE} =-30V, I _B =0			-1
		BDW84A				-1
		BDW84B				-1
		BDW84C				-1
		BDW84D				-1
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-2	mA
h _{FE-1}	DC current gain	I _C =-6A; V _{CE} =-3V	750		20000	
h _{FE-2}	DC current gain	I _C =-15A; V _{CE} =-3V	100			
V _{EC}	Diode forward voltage	I _E =-15A			-3.5	V
t _{on}	Turn-on time	I _C =-10 A, I _{B1} =-I _{B2} =-40 mA R _L =3Ω; V _{BE(off)} =4.2V Duty Cycle≤2%		0.9		Ms
t _{off}	Turn-off time			7.0		Ms

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	0.83	°C/W

Silicon PNP Power Transistors

BDW84/84A/84B/84C/84D

PACKAGE OUTLINE

www.datasheet4u.com

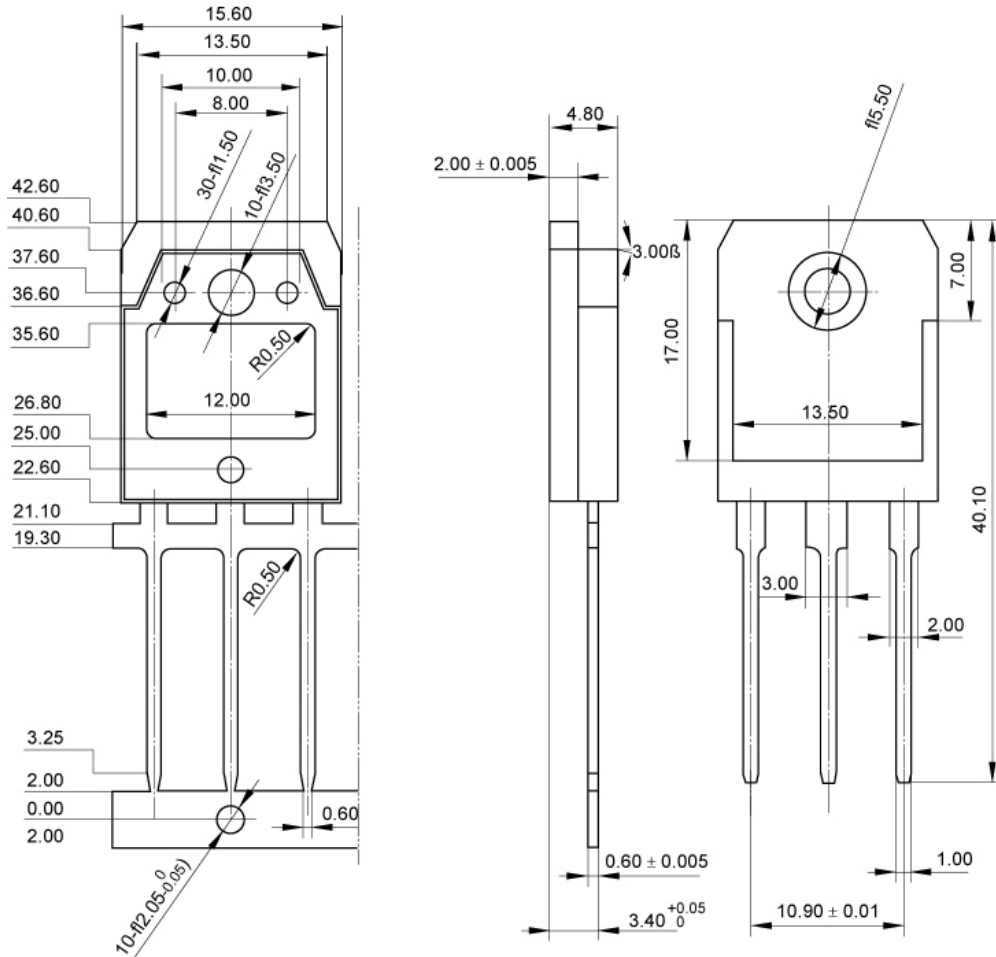


Fig.2 Outline dimensions(unindicated tolerance:±0.1mm)